

## **MM54HC75/MM74HC75** 4-Bit Bistable Latch with Q and $\bar{Q}$ Output

### **General Description**

This 4-bit latch utilizes advanced silicon-gate CMOS technology to achieve the high noise immunity and low power consumption normally associated with standard CMOS integrated circuits. These devices can drive 10 LS-TTL loads.

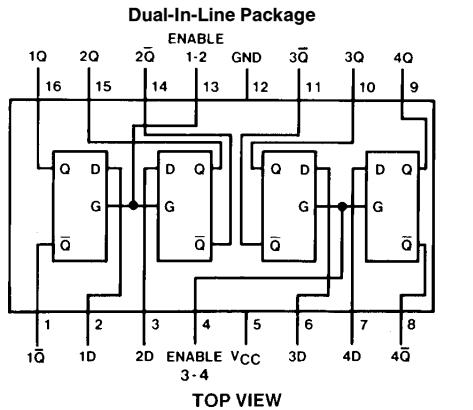
This latch is ideally suited for use as temporary storage for binary information processing, input/output, and indicator units. Information present at the data (D) input is transferred to the Q output when the enable (G) is high. The Q output will follow the data input as long as the enable remains high. When the enable goes low, the information that was present at the data input at the time the transition occurred is retained at the Q output until the enable is permitted to go high again.

The 54HC/74HC logic family is functionally as well as pin-out compatible with the standard 54LS/74LS logic family. All inputs are protected from damage due to static discharge by internal diode clamps to  $V_{CC}$  and ground.

### **Features**

- Typical operating frequency: 50 MHz
- Typical propagation delay: 12 ns
- Wide operating supply voltage range: 2–6V
- Low input current: 1  $\mu$ A maximum
- Low quiescent supply current: 80  $\mu$ A maximum (74HC Series)
- Fanout of 10 LS-TTL loads

### **Connection and Logic Diagrams**



TL/F/5303-1  
Order Number MM54HC75 or MM74HC75

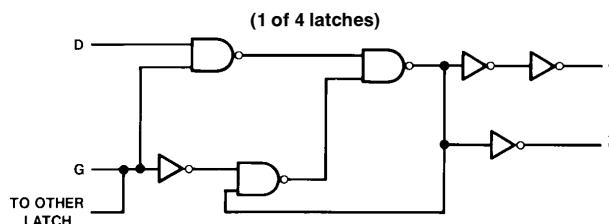
### **Truth Table**

Inputs		Outputs	
D	G	Q	$\bar{Q}$
L	H	L	H
H	H	H	L
X	L	$Q_0$	$\bar{Q}_0$

H = High Level; L = Low Level

X = Don't Care

$Q_0$  = The level of Q before the transition of G



TL/F/5303-2

## Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage ( $V_{CC}$ )	−0.5 to +7.0V
DC Input Voltage ( $V_{IN}$ )	−1.5 to $V_{CC} + 1.5V$
DC Output Voltage ( $V_{OUT}$ )	−0.5 to $V_{CC} + 0.5V$
Clamp Diode Current ( $I_{IK}, I_{OK}$ )	±20 mA
DC Output Current, per pin ( $I_{OUT}$ )	±25 mA
DC $V_{CC}$ or GND Current, per pin ( $I_{CC}$ )	±50 mA
Storage Temperature Range ( $T_{STG}$ )	−65°C to +150°C
Power Dissipation ( $P_D$ ) (Note 3) S.O. Package only	600 mW 500 mW
Lead Temp. ( $T_L$ ) (Soldering 10 seconds)	260°C

## Operating Conditions

	Min	Max	Units
Supply Voltage ( $V_{CC}$ )	2	6	V
DC Input or Output Voltage ( $V_{IN}, V_{OUT}$ )	0	$V_{CC}$	V
Operating Temp. Range ( $T_A$ ) MM74HC	−40	+85	°C
MM54HC	−55	+125	°C
Input Rise or Fall Times ( $t_r, t_f$ )			
	$V_{CC}=2.0V$	1000	ns
	$V_{CC}=4.5V$	500	ns
	$V_{CC}=6.0V$	400	ns

## DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	$V_{CC}$	$T_A = 25^\circ C$		$74HC$	$54HC$	Units
				Typ		$T_A = -40 \text{ to } 85^\circ C$	$T_A = -55 \text{ to } 125^\circ C$	
$V_{IH}$	Minimum High Level Input Voltage		2.0V 4.5V 6.0V	1.5 3.15 4.2		1.5 3.15 4.2	1.5 3.15 4.2	V
$V_{IL}$	Maximum Low Level Input Voltage**		2.0V 4.5V 6.0V	0.5 1.35 1.8		0.5 1.35 1.8	0.5 1.35 1.8	V
$V_{OH}$	Minimum High Level Output Voltage $ I_{OUT}  \leq 20 \mu A$	$V_{IN} = V_{IH}$ or $V_{IL}$	2.0V 4.5V 6.0V	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$V_{IN} = V_{IH}$ or $V_{IL}$ $ I_{OUT}  \leq 4.0 \text{ mA}$ $ I_{OUT}  \leq 5.2 \text{ mA}$	4.5V 6.0V	4.2 5.7	3.98 5.48	3.84 5.34	3.7 5.2	V
$V_{OL}$	Maximum Low Level Output Voltage $ I_{OUT}  \leq 20 \mu A$	$V_{IN} = V_{IH}$ or $V_{IL}$	2.0V 4.5V 6.0V	0 0 0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$V_{IN} = V_{IH}$ or $V_{IL}$ $ I_{OUT}  \leq 4.0 \text{ mA}$ $ I_{OUT}  \leq 5.2 \text{ mA}$	4.5V 6.0V	0.2 0.2	0.26 0.26	0.33 0.33	0.4 0.4	V
$I_{IN}$	Maximum Input Current	$V_{IN} = V_{CC}$ or GND	6.0V		±0.1	±1.0	±1.0	μA
$I_{CC}$	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$	6.0V		4.0	40	80	μA

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: −12 mW/°C from 65°C to 85°C; ceramic "J" package: −12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of  $5V \pm 10\%$  the worst case output voltages ( $V_{OH}$  and  $V_{OL}$ ) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case  $V_{IH}$  and  $V_{IL}$  occur at  $V_{CC}=5.5V$  and 4.5V respectively. (The  $V_{IH}$  value at 5.5V is 3.85V.) The worst case leakage current ( $I_{IN}$ ,  $I_{CC}$ , and  $I_{OZ}$ ) occur for CMOS at the higher voltage and so the 6.0V values should be used.

\*\* $V_{IL}$  limits are currently tested at 20% of  $V_{CC}$ . The above  $V_{IL}$  specification (30% of  $V_{CC}$ ) will be implemented no later than Q1, CY'89.

**AC Electrical Characteristics**  $V_{CC} = 5V$ ,  $T_A = 25^\circ C$ ,  $C_L = 15 \text{ pF}$ ,  $t_r = t_f = 6 \text{ ns}$

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay, Data to Q		14	23	ns
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay, Data to $\bar{Q}$		10	20	ns
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay, Enable to Q		16	27	ns
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay, Enable to $\bar{Q}$		11	23	ns
$t_s$	Minimum Set Up Time			20	ns
$t_H$	Minimum Hold Time		-2	0	ns
$t_W$	Minimum Pulse Width			16	ns

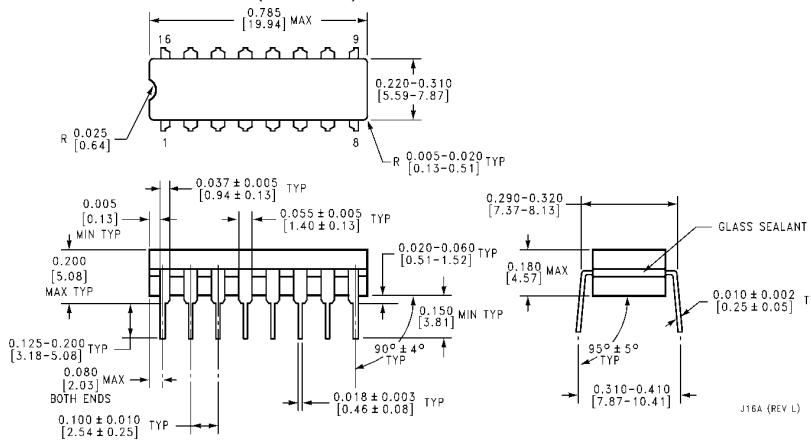
**AC Electrical Characteristics**  $C_L = 50 \text{ pF}$ ,  $t_r = t_f = 6 \text{ ns}$  (unless otherwise specified)

Symbol	Parameter	Conditions	$V_{CC}$	$T_A = 25^\circ C$		$74HC$	$54HC$	Units
				Typ	Guaranteed Limits			
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay, Data to Q		2.0V	37	125	156	188	ns
			4.5V	15	25	32	38	ns
			6.0V	14	24	27	32	ns
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay, Data to $\bar{Q}$		2.0V	29	110	138	165	ns
			4.5V	12	22	28	33	ns
			6.0V	11	19	24	29	ns
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay, Enable to Q		2.0V	40	145	181	218	ns
			4.5V	18	29	36	44	ns
			6.0V	16	25	31	38	ns
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay, Enable to $\bar{Q}$		2.0V	36	125	156	188	ns
			4.5V	15	25	31	38	ns
			6.0V	14	22	28	33	ns
$t_s$	Minimum Set Up Time Data to Enable		2.0V	40	100	125	150	ns
			4.5V	10	20	25	30	ns
			6.0V	9	17	21	25	ns
$t_H$	Minimum Hold Time Enable to Data		2.0V	-10	0	0	0	ns
			4.5V	-2	0	0	0	ns
			6.0V	-2	0	0	0	ns
$t_W$	Minimum Enable Pulse Width		2.0V	40	80	100	120	ns
			4.5V	11	16	20	24	ns
			6.0V	9	14	18	21	ns
$t_{TLH}, t_{THL}$	Maximum Output Rise and Fall Time		2.0V	25	75	95	110	ns
			4.5V	7	15	19	22	ns
			6.0V	6	13	16	19	ns
$C_{PD}$	Power Dissipation Capacitance (Note 5)	(per commonly clocked latched pair)		40				pF
$C_{IN}$	Maximum Input Capacitance			5	10	10	10	pF

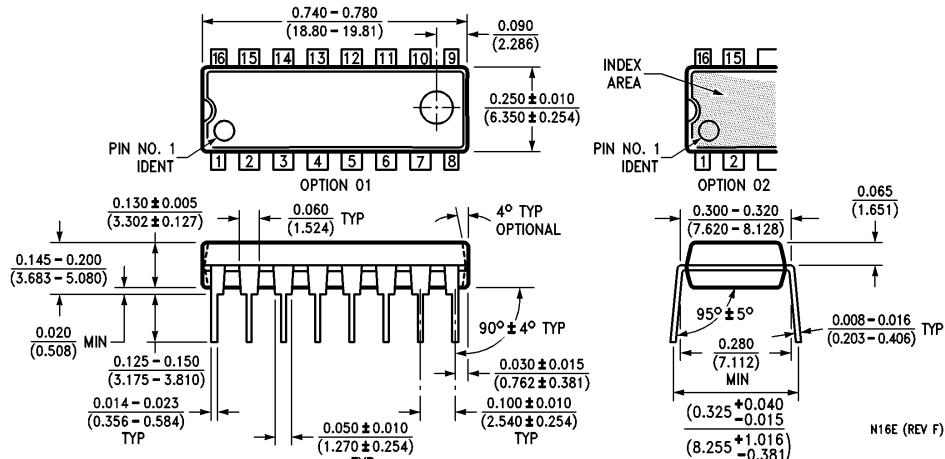
**Note 5:**  $C_{PD}$  determines the no load dynamic power consumption,  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ , and the no load dynamic current consumption,  $I_S = C_{PD} V_{CC} f + I_{CC}$ .

## **MM54HC75/MM74HC75 4-Bit Bistable Latch with Q and $\bar{Q}$ Output**

## **Physical Dimensions** inches (millimeters)



**Order Number MM54HC75J or MM74HC75J  
NS Package J16A**



**Order Number MM54HC75N  
NS Package N16E**

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